



### 70V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25 °C	
-70V	160mΩ @ V <sub>GS</sub> = -10V	-2.6A	
-70V	250mΩ @ V <sub>GS</sub> = -4.5V	-1.6A	

### **Description**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

### **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

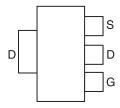
### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
  Solderable per MIL-STD-202, Method 208<sup>3</sup>
- Weight: 0.112 grams (Approximate)

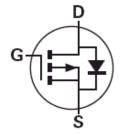




Top View



Pin Out - Top View



Equivalent Circuit

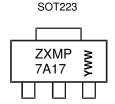
### **Ordering Information** (Note 4)

Part Number	Qualification	Case	Packaging
ZXMP7A17GTA	Commercial	SOT223	1,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



ZXMP7A17 = Product Type Marking Code YWW\_ = Date Code Marking Y or Y = Last Digit of Year (ex: 5= 2015) WW or WW = Week Code (01~53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	-70	V	
Gate-Source Voltage	Gate-Source Voltage		$V_{GS}$	±20	V
		(Note 6)		-3.7	
Continuous Drain Current	$V_{GS} = -10V$	T <sub>A</sub> = +70 °C (Note 6)	$I_{D}$	-2.9	Α
		(Note 5)		-2.6	
Pulsed Drain Current	V <sub>GS</sub> = -10V	(Note 7)	I <sub>DM</sub>	-9.6	Α
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	Is	-4.8	Α
Pulsed Source Current (Body Diode) (Note 7)		I <sub>SM</sub>	-9.6	A	

### Thermal Characteristics (@TA = +25 ℃, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2.0 16.0	W mW/℃	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	3.9 31		
Thermal Resistance, Junction to Ambient	(Note 5)	B	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	34		
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	∞	

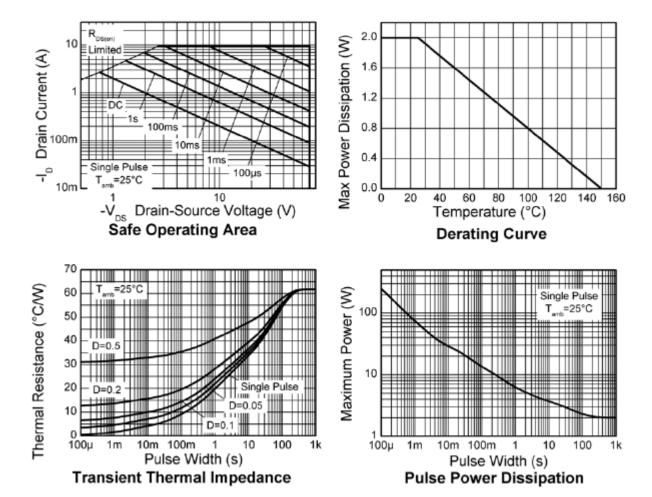
# Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	$BV_{DSS}$	-70	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -70V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS						·	
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0		_	V	$I_{D}$ = -250 $\mu$ A, $V_{DS}$ = $V_{GS}$	
Static Drain-Source On-Resistance (Note 8)				0.16	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.1A	
Static Drain-Source On-Nesistance (Note 6)	R <sub>DS(ON)</sub>		_	0.25	12	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.7A	
Forward Transconductance (Notes 8 & 9)	g <sub>fs</sub>	_	4.4	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.1A	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	-0.85	-0.95	V	I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V	
Reverse recovery time (Note 9)	t <sub>rr</sub>	_	29.8	_	ns	I <sub>S</sub> = -2.1A, di/dt= 100A/μs	
Reverse recovery charge (Note 9)	$Q_{rr}$	_	38.5	_	nC		
DYNAMIC CHARACTERISTICS (Note 9)						·	
Input Capacitance	C <sub>iss</sub>		635		рF	101/11/101/	
Output Capacitance	Coss		52	_	рF	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V -f= 1MHz	
Reverse Transfer Capacitance	$C_{rss}$	_	42.5	_	pF		
Total Gate Charge (Note 10)	Qg	_	9.6	_	nC	V <sub>GS</sub> = -5V	
Total Gate Charge (Note 10)	Qg	_	18	_	nC	V <sub>DS</sub> = -35V	
Gate-Source Charge (Note 10)	$Q_{gs}$	_	1.77		nC	V <sub>GS</sub> = -10V	
Gate-Drain Charge (Note 10)	$Q_{gd}$	_	3.66		nC		
Turn-On Delay Time (Note 10)	t <sub>D(on)</sub>	_	2.5		ns		
Turn-On Rise Time (Note 10)	tr	-	3.4		ns	$V_{DD}$ = -35V, $V_{GS}$ = -10V $I_{D}$ = -1A, $R_{G} \approx 6.0\Omega$	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$		27.9	_	ns		
Turn-Off Fall Time (Note 10)	t <sub>f</sub>		8	_	ns		

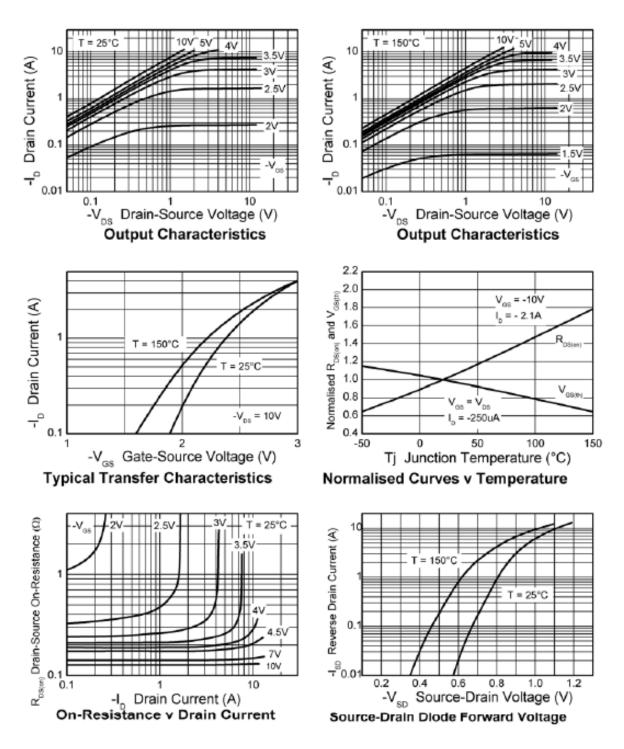
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at  $t \le 5$  seconds.
- 7. Same as Note 5, except the device is midded with D= 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%.$
- 9. For design aid only, not subject to production testing.
- 10. Switching characteristics are independent of operating junction temperatures.

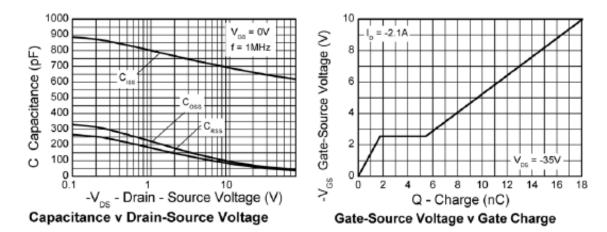






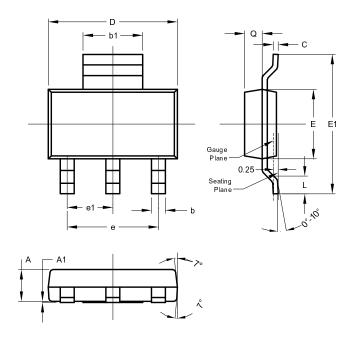






### **Package Outline Dimensions**

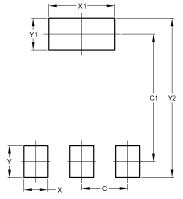
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
<b>A</b> 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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